

IN THE CLAIMS

Claims 1-11 (Canceled)

12. (New) A communication semiconductor integrated circuit device comprising:

a transmission unit formed on a semiconductor chip, and forming a transmission signal to be provided to an antenna;

a reception unit formed on the semiconductor chip, and receiving a receiving signal from the antenna and forming a signal which has a frequency lower than that of the receiving signal, wherein the reception unit includes a low noise amplifier transistor receiving the receiving signal;

a terminal formed on the semiconductor chip, and coupled to the low noise amplifier transistor;

a first voltage line arranged to be supplied with a first voltage having a first potential;

a second voltage line arranged to be supplied with a second voltage having a second potential that is different from the first potential; and

a protection unit formed on the semiconductor chip, and coupled to the low noise amplifier transistor, to the first voltage line, to the second voltage line and the terminal, wherein the protection unit includes a first protection circuit which is coupled between the first voltage

line and the terminal and which allows an electric current to flow from the first voltage line to the terminal at a protection time against an electrostatic breakdown, and a second protection circuit which is coupled between the second voltage line and the terminal and which allows an electric current to flow from the terminal to the second voltage line at a protection time against an electrostatic breakdown.

13. (New) A communication semiconductor integrated circuit device according to claim 12, wherein the terminal is arranged to be supplied with the receiving signal from the antenna.

14. (New) A communication semiconductor integrated circuit device according to claim 12, wherein an output of the low noise amplifier transistor is supplied to the terminal.

15. (New) A communication semiconductor integrated circuit device according to claim 12, wherein the protection unit further comprises:

a third protection circuit which is coupled between the first voltage line and the terminal and which allows an electric current to flow from the terminal to the first voltage line at a protection time against an electrostatic breakdown, and

a fourth protection circuit which is coupled between the second voltage line and the terminal and which allows an electric current to flow from the second voltage line to the terminal at a protection time against an electrostatic breakdown.

16. (New) A communication semiconductor integrated circuit device according to claim 15, wherein the second potential is lower than the first potential.

17. (New) A communication semiconductor integrated circuit device according to claim 12, wherein each of the first protection circuit and the second protection circuit includes a MOSFET.

18. (New) A communication semiconductor integrated circuit device according to claim 13, wherein each of the first protection circuit and the second protection circuit includes a MOSFET.

19. (New) A communication semiconductor integrated circuit device according to claim 14, wherein each of the first protection circuit and the second protection circuit includes a MOSFET.

20. (New) A communication semiconductor integrated circuit device according to claim 16, wherein each of the first protection circuit and the second protection circuit includes a MOSFET.

21. (New) A communication semiconductor integrated circuit device according to claim 12, wherein the second potential is lower than that first potential.

22. (New) A communication semiconductor integrated circuit device according to claim 13, wherein the second potential is lower than the first potential.

23. (New) A communication semiconductor integrated circuit device according to claim 14, wherein the second potential is lower than the first potential.

24. (New) A communication semiconductor integrated circuit device according to claim 12, wherein the first potential is lower than the second potential.

25. (New) A communication semiconductor integrated circuit device according to claim 13, wherein the first potential is lower than the second potential.

26. (New) A communication semiconductor integrated circuit device according to claim 14, wherein the first potential is lower than the second potential.

27. (New) A communication semiconductor integrated circuit device according to claim 12, wherein the low noise amplifier transistor includes a bipolar transistor.

28. (New) A communication semiconductor integrated circuit device according to claim 17, wherein the low noise amplifier transistor includes a bipolar transistor.

29. (New) A communication semiconductor integrated circuit device according to claims 18, wherein the low noise amplifier transistor includes a bipolar transistor.

30. (New) A communication semiconductor integrated circuit device according to claims 19, wherein the low noise amplifier transistor includes a bipolar transistor.

31. (New) A communication semiconductor integrated circuit device according to claims 20, wherein the low noise amplifier transistor includes a bipolar transistor.